L Number	Hits	Search Text	DB	Time stamp
1	114	@ad<=20001107 and 'bottom gate TFT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 08:50
-	36	@ad<=20001107 and 'thin film transistor' and 'selective' near 'doping'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:55
-	2	@ad<=20001107 and 'thin film transistor' and 'cleaning' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 14:53
-	1	@ad<=20001107 and 'TFT' and 'cleaning' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 14:53
-	18	@ad<=20001107 and 'TFT' and 'remove' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:10
-	7	@ad<=20001107 and 'TFT' and 'removal' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 15:06
-	590	@ad<=20001107 and "thin film transistor" and "ohmic contact layer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 15:26
-	60	@ad<=20001107 and "thin film transistor" and "remove" near 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 08:43
-	1	"3859716".PN.	USPAT	2002/07/16 17:05
-	1	"4757026".PN.	USPAT	2002/07/16 17:05
-	1	"4876213".PN.	USPAT	2002/07/16 17:05
-	1	"5182620".PN.	USPAT	2002/07/16 17:06
-	1	"5266823".PN.	USPAT	2002/07/16 17:06
-	1	"5323042".PN.	USPAT	2002/07/16 17:06
-	1	"5998841".PN.	USPAT	2002/07/16 17:06
-	1	"5962872".PN.	USPAT	2002/07/16 17:06
-	1	"5939731".PN.	USPAT	2002/07/16 17:07
-	1	"5804471".PN.	USPAT	2002/07/16 17:07
-	1	"5856689".PN.	USPAT	2002/07/16 17:08
-	1	"5804471".PN.	USPAT	2002/07/16 17:08
-	3055	((438/149) or (438/158) or (438/315) or (438/334)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:39
-	6	(((438/149) or (438/158) or (438/315) or (438/334)).CCLS.) and @ad<=20001107 and "thin film transistor" and "remove" near 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:50
-	608	(((438/149) or (438/158) or (438/315) or (438/334)).CCLS.) and @ad<=20001107 and "thin film transistor"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 08:46

-	5525	((438/149) or (438/158-159) or (438/315) or (438/334) or (438/163) or (438/166) or (257/69) or (257/72) or (257/59)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:43
-	16	(((438/149) or (438/158-159) or (438/315) or (438/334) or (438/163) or (438/166) or (257/69) or (257/72) or (257/59)).CCLS.) and @ad<=20001107 and "thin film transistor" and "remove" near 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:51
-	1	@ad<=20001107 and 'thin film transistor' and 'buried gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:56
-	30430	@ad<=20001107 and 'thin film transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:59
-	779	(@ad<=20001107 and 'thin film transistor') and short same channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:01
-	719	(@ad<=20001107 and 'thin film transistor') and short same channel and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:02
-	18	@ad<=20001107 and 'TFT' and 'remove' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 08:50
-	1	"5641974".PN.	USPAT	2002/12/17 16:13
-	1	"5780871".PN.	USPAT	2002/12/17 16:13
-	1	"5837619".PN.	USPAT	2002/12/17 16:14
-	1	"5882165".PN.	USPAT	2002/12/17 16:14
-	1	"5917571".PN.	USPAT	2002/12/17 16:14
-	1	"6177302".PN.	USPAT	2002/12/17 16:14
-	4767	((257/59) or (257/61) or (257/72) or (257/347) or (349/42-43)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:18

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1	114	@ad<=20001107 and 'bottom gate TFT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 08:50
-	36	@ad<=20001107 and 'thin film transistor' and 'selective' near 'doping'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:55
-	2	@ad<=20001107 and 'thin film transistor' and 'cleaning' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 14:53
-	1	@ad<=20001107 and 'TFT' and 'cleaning' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 14:53
-	18	@ad<=20001107 and 'TFT' and 'remove' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:10
-	7	@ad<=20001107 and 'TFT' and 'removal' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 15:06
-	590	@ad<=20001107 and "thin film transistor" and "ohmic contact layer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 15:26
-	60	@ad<=20001107 and "thin film transistor" and "remove" near 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 08:43
-	1	"3859716".PN.	USPAT	2002/07/16 17:05
-	1	"4757026".PN.	USPAT	2002/07/16 17:05
-	1	"4876213".PN.	USPAT	2002/07/16 17:05
-	1	"5182620".PN.	USPAT	2002/07/16 17:06
-	1	"5266823".PN.	USPAT	2002/07/16 17:06
-	1	"5323042".PN.	USPAT	2002/07/16 17:06
-	1	"5998841".PN.	USPAT	2002/07/16 17:06
-	1	"5962872".PN.	USPAT	2002/07/16 17:06
-	1	"5939731".PN.	USPAT	2002/07/16 17:07
-	1	"5804471".PN.	USPAT	2002/07/16 17:07
-	1	"5856689".PN.	USPAT	2002/07/16 17:08
-	1	"5804471".PN.	USPAT	2002/07/16 17:08
-	3055	((438/149) or (438/158) or (438/315) or (438/334)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:39
-	6	(((438/149) or (438/158) or (438/315) or (438/334)).CCLS.) and @ad<=20001107 and "thin film transistor" and "remove" near 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:50
-	608	(((438/149) or (438/158) or (438/315) or (438/334)).CCLS.) and @ad<=20001107 and "thin film transistor"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 08:46

–	5525	((438/149) or (438/158-159) or (438/315) or (438/334) or (438/163) or (438/166) or (257/69) or (257/72) or (257/59)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:43
–	16	(((438/149) or (438/158-159) or (438/315) or (438/334) or (438/163) or (438/166) or (257/69) or (257/72) or (257/59)).CCLS.) and @ad<=20001107 and "thin film transistor" and "remove" near 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:51
–	1	@ad<=20001107 and 'thin film transistor' and 'burried gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:56
–	30430	@ad<=20001107 and 'thin film transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:59
–	779	(@ad<=20001107 and 'thin film transistor') and short same channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:01
–	719	(@ad<=20001107 and 'thin film transistor') and short same channel and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:02
–	18	@ad<=20001107 and 'TFT' and 'remove' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 08:50
–	1	"5641974".PN.	USPAT	2002/12/17 16:13
–	1	"5780871".PN.	USPAT	2002/12/17 16:13
–	1	"5837619".PN.	USPAT	2002/12/17 16:14
–	1	"5882165".PN.	USPAT	2002/12/17 16:14
–	1	"5917571".PN.	USPAT	2002/12/17 16:14
–	1	"6177302".PN.	USPAT	2002/12/17 16:14
–	4767	((257/59) or (257/61) or (257/72) or (257/347) or (349/42-43)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:18